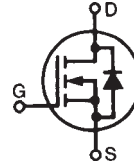


PolarHT™ Power MOSFET

IXTK 100N25P
IXTQ 100N25P
IXTT 100N25P

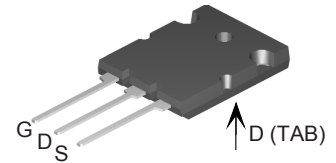
V_{DSS} = 250 V
I_{D25} = 100 A
R_{DS(on)} ≤ 27 mΩ

N-Channel Enhancement Mode
Avalanche Rated

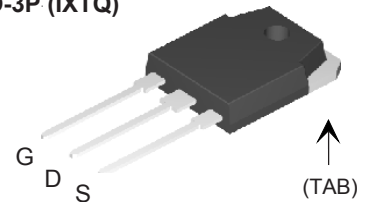


Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	T _J = 25° C to 150° C	250	V
V_{DGR}	T _J = 25° C to 150° C; R _{GS} = 1 MΩ	250	V
V_{GSS}	Continuous	±20	V
V_{GSM}	Transient	±30	V
I_{D25}	T _C = 25° C	100	A
I_{D(RMS)}	External lead current limit	75	A
I_{DM}	T _C = 25° C, pulse width limited by T _{JM}	250	A
I_{AR}	T _C = 25° C	60	A
E_{AR}	T _C = 25° C	60	mJ
E_{AS}	T _C = 25° C	2.0	J
dv/dt	I _S ≤ I _{DM} , di/dt ≤ 100 A/μs, V _{DD} ≤ V _{DSS} , T _J ≤ 150° C, R _G = 4 Ω	10	V/ns
P_D	T _C = 25° C	600	W
T_J		-55 ... +150	°C
T_{JM}		150	°C
T_{stg}		-55 ... +150	°C
T_L	1.6 mm (0.062 in.) from case for 10 s	300	°C
T_{SOLD}	Plastic body for 10 s	260	°C
M_d	Mounting torque	1.13/10	Nm/lb.in.
Weight	TO-3P	5.5	g
	TO-264	10	g
	TO-268	5.0	g

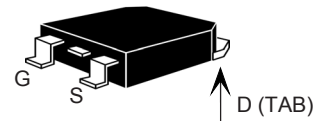
TO-264 (IXTK)



TO-3P (IXTQ)



TO-268 (IXTT)



G = Gate D = Drain
S = Source TAB = Drain

Features

- International standard packages
- Unclamped Inductive Switching (UIS) rated
- Low package inductance
 - easy to drive and to protect

Advantages

- Easy to mount
- Space savings
- High power density

Symbol	Test Conditions (T _J = 25° C, unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{DSS}	V _{GS} = 0 V, I _D = 250 μA	250		V
V_{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	2.5		5.0 V
I_{GSS}	V _{GS} = ±20 V _{DC} , V _{DS} = 0			±100 nA
I_{DSS}	V _{DS} = V _{DSS}			25 μA
	V _{GS} = 0 V T _J = 125° C			250 μA
R_{DS(on)}	V _{GS} = 10 V, I _D = 0.5 I _{D25} Pulse test, t ≤ 300 μs, duty cycle d ≤ 2 %			27 mΩ

Symbol	Test Conditions	Characteristic Values (T _J = 25° C, unless otherwise specified)		
		Min.	Typ.	Max.
g_{fs}	V _{DS} = 10 V; I _D = 0.5 I _{D25} , pulse test	40	56	S
C_{iss}	V _{GS} = 0 V, V _{DS} = 25 V, f = 1 MHz		6300	pF
C_{oss}			1150	pF
C_{rss}			240	pF
t_{d(on)}	V _{GS} = 10 V, V _{DS} = 0.5 V _{DSS} , I _D = I _{D25} R _G = 3.3 Ω (External)		25	ns
t_r			26	ns
t_{d(off)}			100	ns
t_f			28	ns
Q_{g(on)}	V _{GS} = 10 V, V _{DS} = 0.5 V _{DSS} , I _D = 0.5 I _{D25}		185	nC
Q_{gs}			43	nC
Q_{gd}			91	nC
R_{thJC}	TO-3P		0.21	0.21° C/W
R_{thCS}				° C/W
R_{thCS}	TO-264		0.15	° C/W

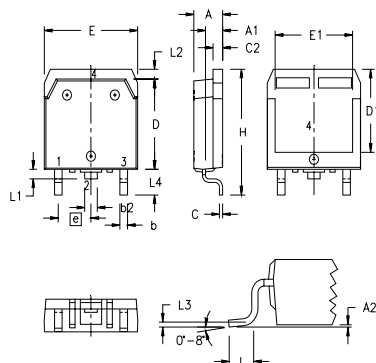
Source-Drain Diode

Characteristic Values

($T_1 = 25^\circ \text{C}$, unless otherwise specified)

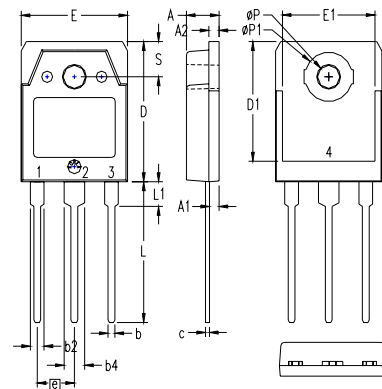
Symbol	Test Conditions	Min.	Typ.	Max.
I_S	$V_{GS} = 0 \text{ V}$			100 A
I_{SM}	Repetitive			250 A
V_{SD}	$I_F = I_S, V_{GS} = 0 \text{ V},$ Pulse test, $t \leq 300 \mu\text{s}$, duty cycle $d \leq 2 \%$			1.5 V
t_{rr}	$I_F = 25 \text{ A}, -di/dt = 100 \text{ A}/\mu\text{s}$ $V_R = 100 \text{ V}, V_{GS} = 0 \text{ V}$		200	ns
Q_{RM}			3.0	μC

TO-268 (IXTT) Outline



SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.193	.201	4.90	5.10
A1	.106	.114	2.70	2.90
B	.001	.010	0.02	0.25
B2	.045	.057	1.15	1.45
C	.016	.026	0.40	0.65
C2	.057	.063	1.45	1.60
D	.543	.551	13.80	14.00
D1	.488	.500	12.40	12.70
E	.624	.632	15.85	16.05
E1	.524	.535	13.30	13.60
e	.215 BSC		5.45 BSC	
H	.736	.752	18.70	19.10
L	.094	.106	2.40	2.70
L1	.047	.055	1.20	1.40
L2	.039	.045	1.00	1.15
L3	.010 BSC		0.25 BSC	
L4	.150	.161	3.80	4.10

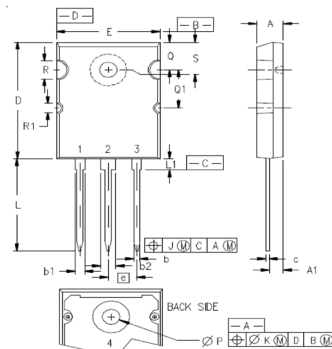
TO-3P (IXTQ) Outline



- 1 - GATE
- 2 - DRAIN (COLLECTOR)
- 3 - SOURCE (EMITTER)
- 4 - DRAIN (COLLECTOR)

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.185	.193	4.70	4.90
A1	.051	.059	1.30	1.50
A2	.057	.065	1.45	1.65
b	.035	.045	0.90	1.15
b2	.075	.087	1.90	2.20
b4	.114	.126	2.90	3.20
c	.022	.031	0.55	0.80
D	.780	.799	19.80	20.30
D1	.665	.677	16.90	17.20
E	.610	.622	15.50	15.80
E1	.531	.539	13.50	13.70
e	.215 BSC		5.45 BSC	
L	.779	.795	19.80	20.20
L1	.134	.142	3.40	3.60
ØP	.126	.134	3.20	3.40
ØP1	.272	.280	6.90	7.10
S	.193	.201	4.90	5.10

TO-264 (IXTK) Outline



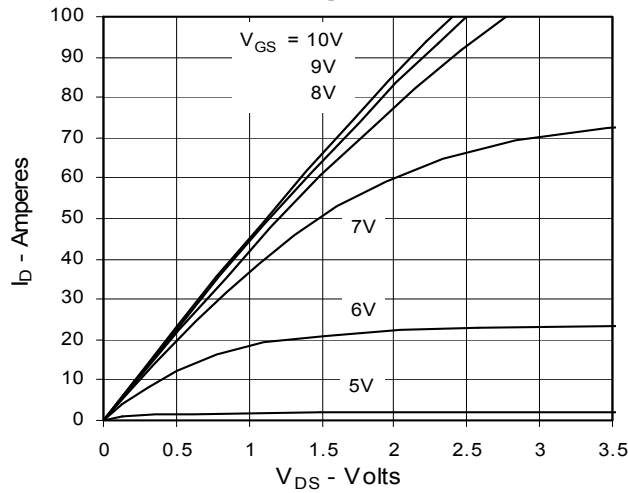
- 1 - GATE
2, 4 - DRAIN (COLLECTOR)
3 - SOURCE (EMITTER)

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.185	.209	4.70	5.31
A1	.102	.118	2.59	3.00
b	.037	.055	0.94	1.40
b1	.087	.102	2.21	2.59
b2	.110	.126	2.79	3.20
c	.017	.029	0.43	0.74
D	1.007	1.047	25.58	26.59
E	.760	.799	19.30	20.29
	.215 BSC		5.46 BSC	
J	.000	.010	0.00	0.25
K	.000	.010	0.00	0.25
L	.779	.842	19.79	21.39
L1	.087	.102	2.21	2.59
ØP	.122	.138	3.10	3.51
Q	.240	.256	6.10	6.50
Q1	.330	.346	8.38	8.79
ØR	.155	.187	3.94	4.75
ØR1	.085	.093	2.16	2.36
S	.243	.253	6.17	6.43

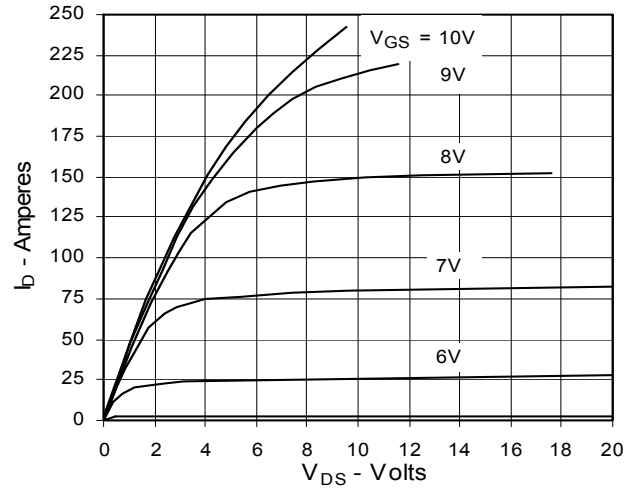
IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585
	4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405B2	6,759,692
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2

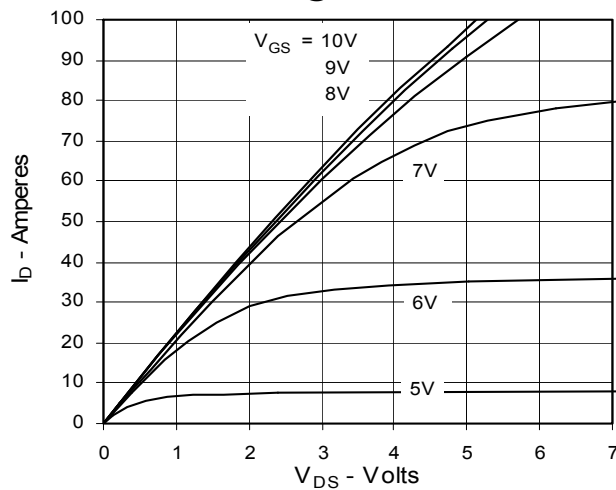
**Fig. 1. Output Characteristics
@ 25°C**



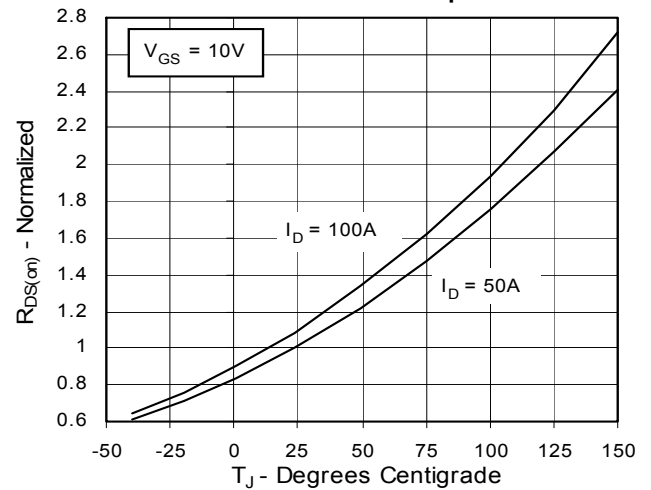
**Fig. 2. Extended Output Characteristics
@ 25°C**



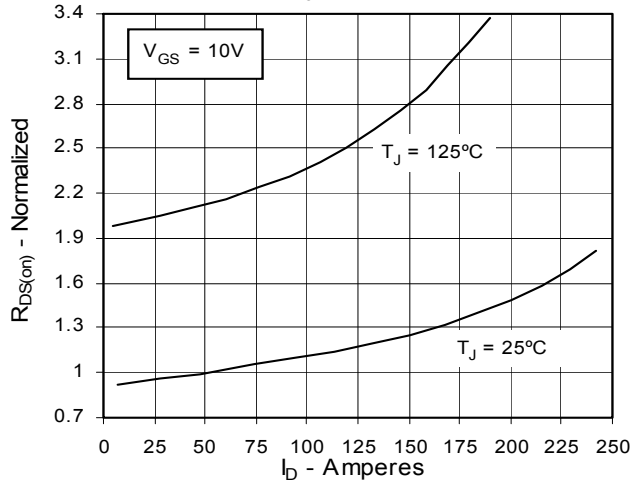
**Fig. 3. Output Characteristics
@ 125°C**



**Fig. 4. $R_{DS(on)}$ Normalized to 0.5 I_{D25}
Value vs. Junction Temperature**



**Fig. 5. $R_{DS(on)}$ Normalized to
0.5 I_{D25} Value vs. I_D**



**Fig. 6. Drain Current vs. Case
Temperature**

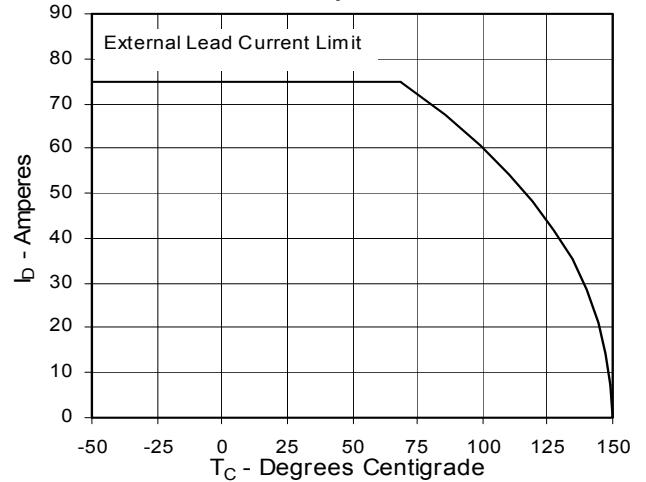


Fig. 7. Input Admittance

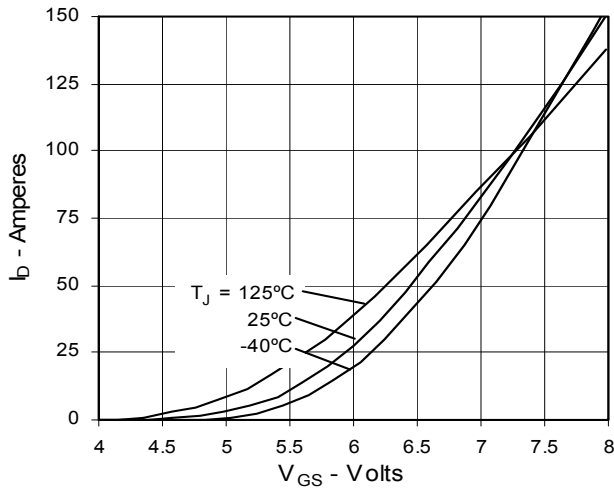


Fig. 8. Transconductance

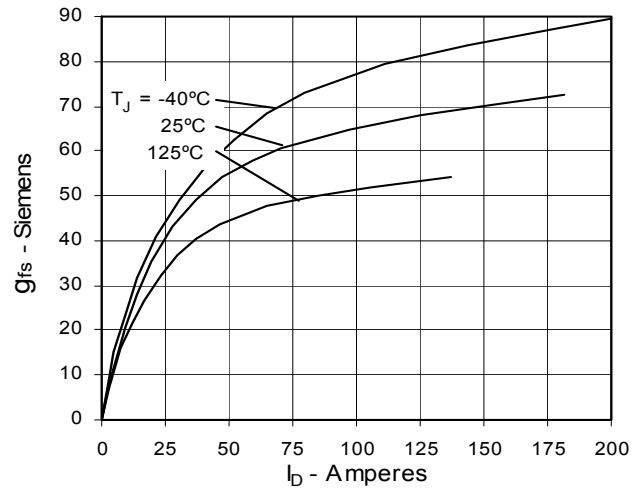


Fig. 9. Source Current vs. Source-To-Drain Voltage

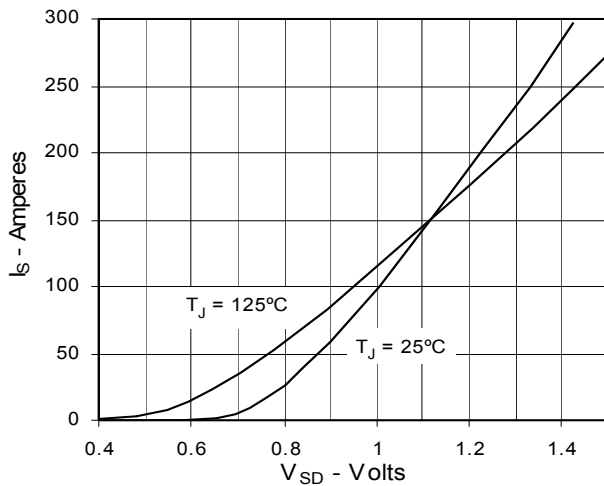


Fig. 10. Gate Charge

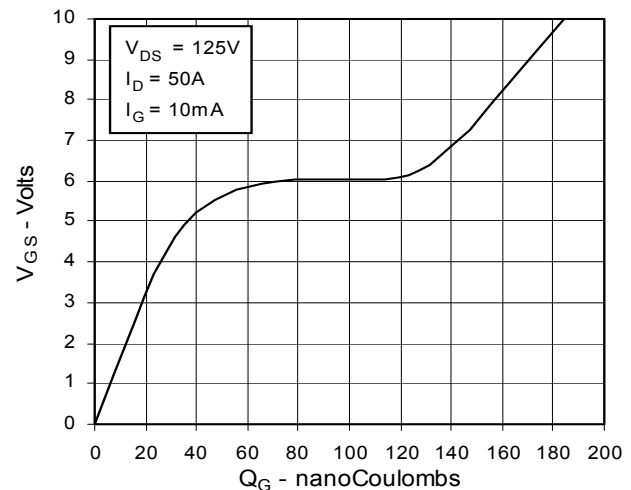


Fig. 11. Capacitance

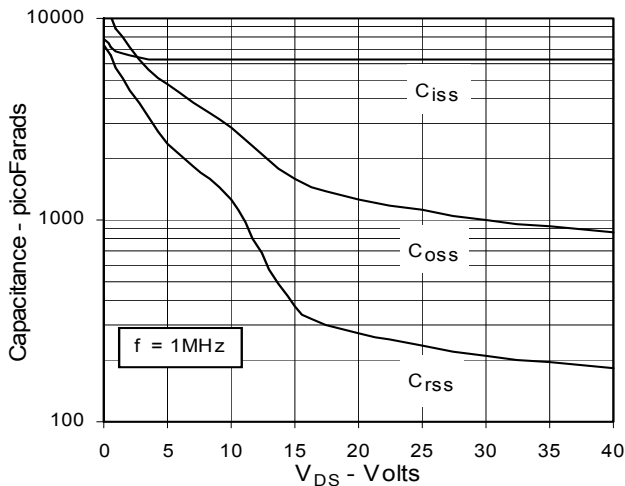


Fig. 12. Forward-Bias Safe Operating Area

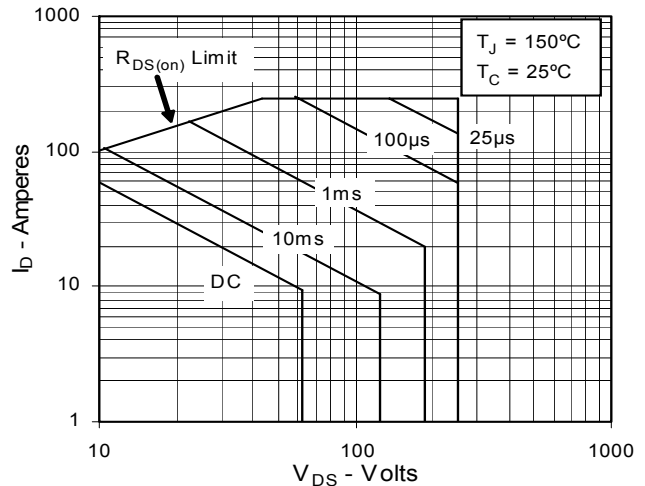
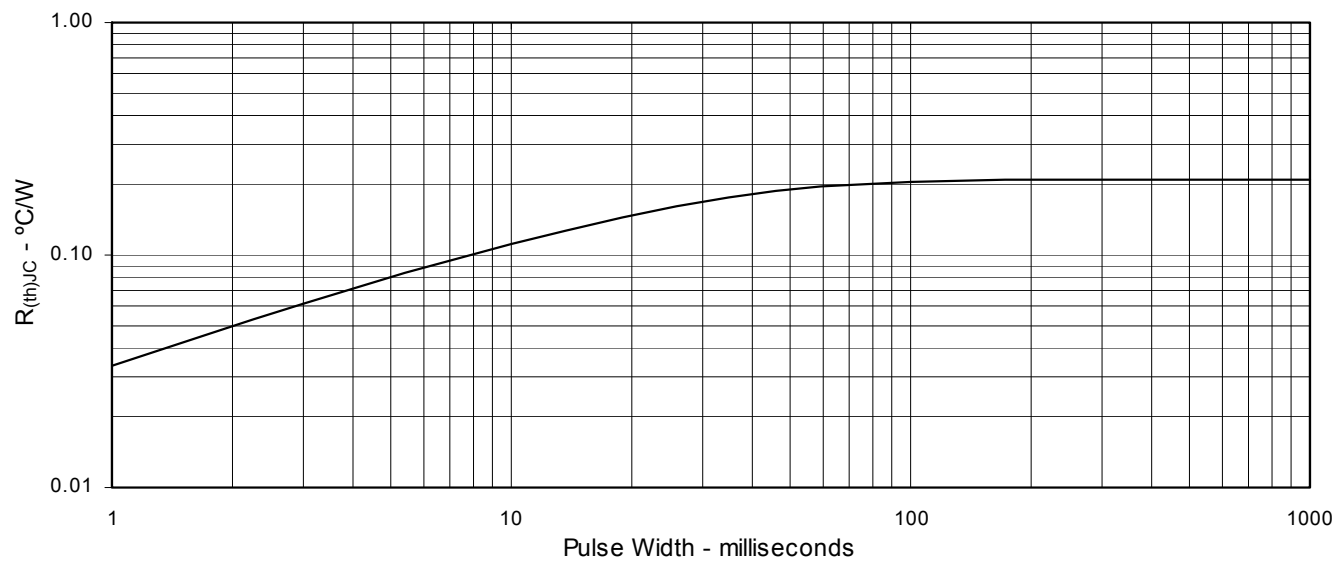


Fig. 13. Maximum Transient Thermal Resistance



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